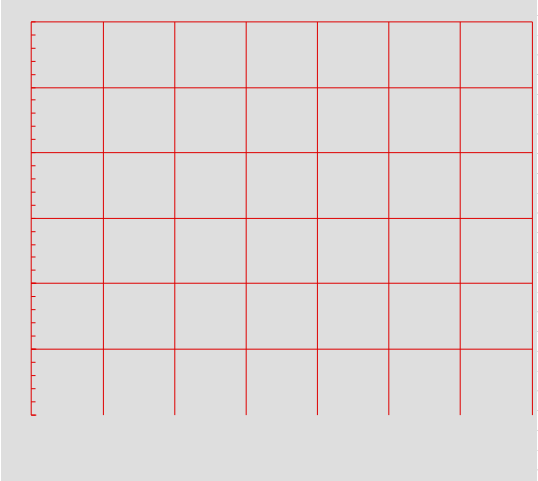
| | | | |
|---|---|---|---|
| Average gate power dissipation ($T_j$=125 ) | $P_{G(AV)}$ | 0.5 | W |
| Peak gate power | $P_{GM}$ | 10 | W |
| Peak pulse voltage ($T_j$=25 ; non-repetitive,off-state;FIG.7) | $V_{pp}$ | 3.5 | kV |

**ELECTRICAL CHARACTERISTICS** ($T_j$=25 unless otherwise specified)

| | | | | | |
|---|---|---|---|---|---|
| | | | | | |
| $I_{GT}$ | $V_D$ =12V $R_L$ =33Ω | - - | MAX. | 10 | mA |
| $V_{GT}$ | | - - | MAX. | 1 | V |
| $V_{GD}$ | $V_D$ =$V_{DRM}$ $T_j$ =125 $R_L$ =3.3kΩ | - - | MIN. | 0.2 | V |
| $I_L$ | $I_G$ =1.2$I_{GT}$ | - | MAX. | 20 | mA |
| | | | | 35 | |
| $I_H$ | $I_T$ =100mA | | MAX. | 20 | mA |
| dV/dt | $V_D$=540V Gate Open $T_j$ =125 | | MIN. | 500 | |

Maximum power dissipation versus RMS on-state current



RMS on-state current versus case temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards

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